

NTHD4P02F

Power MOSFET and Schottky Diode

–20 V, –3.0 A, Single P–Channel with
3.0 A Schottky Barrier Diode, ChipFET™

Features

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP–6 Package with Similar Thermal Characteristics
- Independent Pinout to each Device to Ease Circuit Design
- Ultra Low V_F Schottky
- Pb–Free Package is Available

Applications

- Li–Ion Battery Charging
- High Side DC–DC Conversion Circuits
- High Side Drive for Small Brushless DC Motors
- Power Management in Portable, Battery Powered Products

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Units
Drain-to–Source Voltage			V_{DS}	–20	V
Gate-to–Source Voltage			V_{GS}	± 12	V
Continuous Drain Current	Steady State	$T_J = 25^\circ\text{C}$	I_D	–2.2	A
		$T_J = 85^\circ\text{C}$		–1.6	
	$t \leq 5 \text{ s}$	$T_J = 25^\circ\text{C}$	I_D	–3.0	A
Pulsed Drain Current	$t_p = 10 \mu\text{s}$		I_{DM}	–9.0	A
Power Dissipation	Steady State	$T_J = 25^\circ\text{C}$	P_D	1.1	W
		$T_J = 85^\circ\text{C}$		0.6	
	$t \leq 5 \text{ s}$	$T_J = 25^\circ\text{C}$		2.1	
Continuous Source Current (Body Diode)			I_S	–2.1	A
Operating Junction and Storage Temperature			T_J, T_{STG}	–55 to 150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

SCHOTTKY DIODE MAXIMUM RATINGS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Units
Peak Repetitive Reverse Voltage			V_{RRM}	20	V
DC Blocking Voltage			V_R	20	V
Average Rectified Forward Current	Steady State	$T_J = 25^\circ\text{C}$	I_F	2.2	A
	$t \leq 5 \text{ s}$			3.0	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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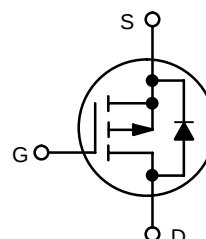
<http://onsemi.com>

MOSFET

$V_{(BR)DS}$	$R_{DS(on)}$ TYP	I_D MAX
–20 V	–130 m Ω @ –4.5 V	–3.0 A
	200 m Ω @ –2.5 V	

SCHOTTKY DIODE

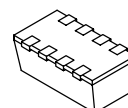
V_R MAX	V_F TYP	I_F MAX
20 V	0.510 V	3.0 A



P–Channel MOSFET

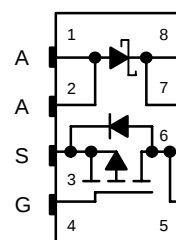


SCHOTTKY DIODE

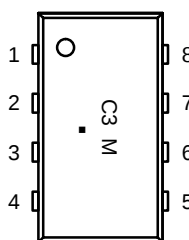


ChipFET
CASE 1206A
STYLE 3

PIN CONNECTIONS



MARKING DIAGRAM



C3 = Specific Device Code
M = Month Code
▪ = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTHD4P02FT1	ChipFET	3000/Tape & Reel
NTHD4P02FT1G	ChipFET (Pb–free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTHD4P02F

THERMAL RESISTANCE RATINGS

Parameter			Symbol	Max	Units
Junction-to-Ambient (Note 1)	Steady State	$T_J = 25^{\circ}\text{C}$	$R_{\theta JA}$	110	$^{\circ}\text{C/W}$
	$t \leq 5 \text{ s}$			60	

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.27 in sq [1 oz] including traces).

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	-23		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$			-1.0	μA
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^{\circ}\text{C}$			-5.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250 \mu\text{A}$	-0.6	-0.75	-1.2	V
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$		0.130	0.155	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -1.7 \text{ A}$		0.200	0.240	
Forward Transconductance	g_{FS}	$V_{DS} = -10 \text{ V}, I_D = -1.7 \text{ A}$		5.0		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}, V_{DS} = -10 \text{ V}$		185	300	pF
Output Capacitance	C_{OSS}			95	150	
Reverse Transfer Capacitance	C_{RSS}			30	50	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V}, I_D = -2.2 \text{ A}$		3.0	6.0	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	Q_{GS}			0.5		
Gate-to-Drain Charge	Q_{GD}			0.9		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5 \text{ V}, V_{DD} = -16 \text{ V}, I_D = -2.2 \text{ A}, R_G = 2.5 \Omega$		7.0	12	ns
Rise Time	t_r			13	25	
Turn-Off Delay Time	$t_{d(OFF)}$			33	50	
Fall Time	t_f			27	40	

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 2)

Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = -2.1 \text{ A}$		-0.85	-1.15	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0 \text{ V}, I_S = -2.1 \text{ A}, di_S/dt = 100 \text{ A}/\mu\text{s}$		32		ns
Charge Time	t_a			10		
Discharge Time	t_b			22		
Reverse Recovery Charge	Q_{RR}			15		nC

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1 \text{ A}$		0.425		V
		$I_F = 0.5 \text{ A}$		0.480		
		$I_F = 1.0 \text{ A}$		0.510	0.575	
Maximum Instantaneous Reverse Current	I_R	$V_R = 10 \text{ V}$			1.0	μA
		$V_R = 20 \text{ V}$			5.0	
Maximum Voltage Rate of Change	dv/dt	$V_R = 20 \text{ V}$		10,000		V/ns
Non-Repetitive Peak Surge Current	I_{FSM}	Halfwave, Single Pulse, 60 Hz			23	A

2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL MOSFET PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

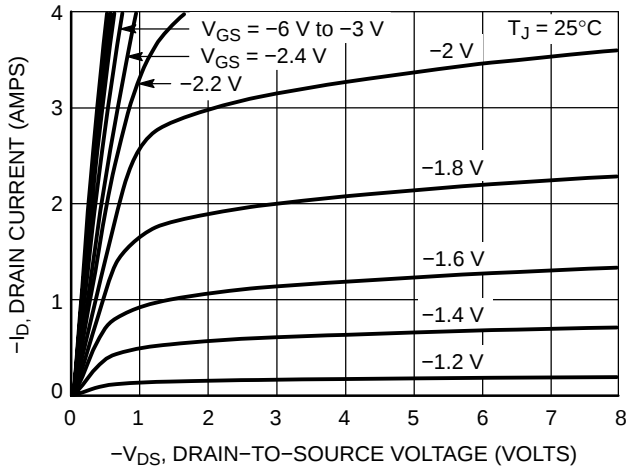


Figure 1. On-Region Characteristics

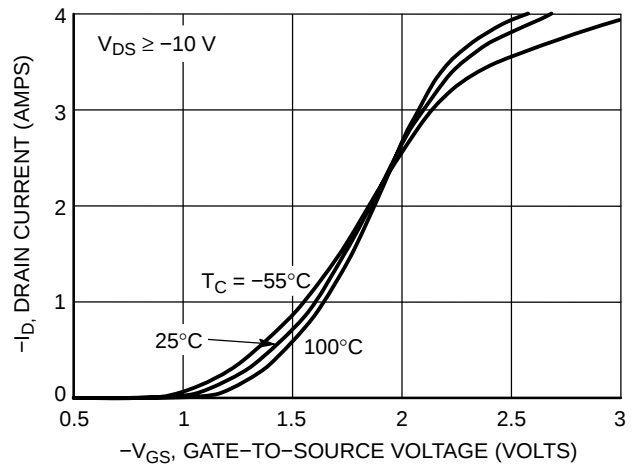


Figure 2. Transfer Characteristics

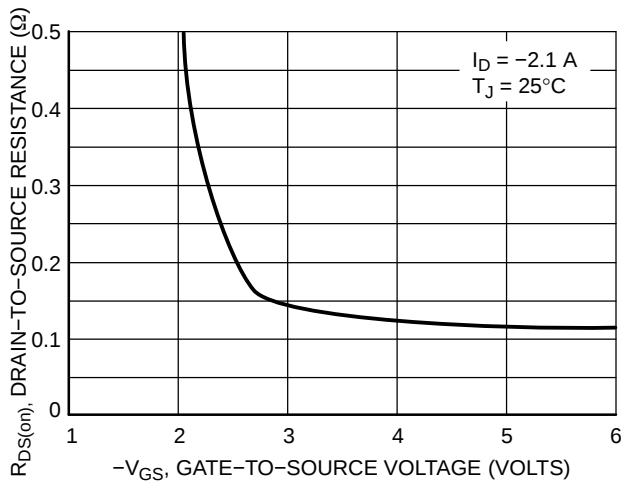


Figure 3. On-Resistance vs. Gate-to-Source Voltage

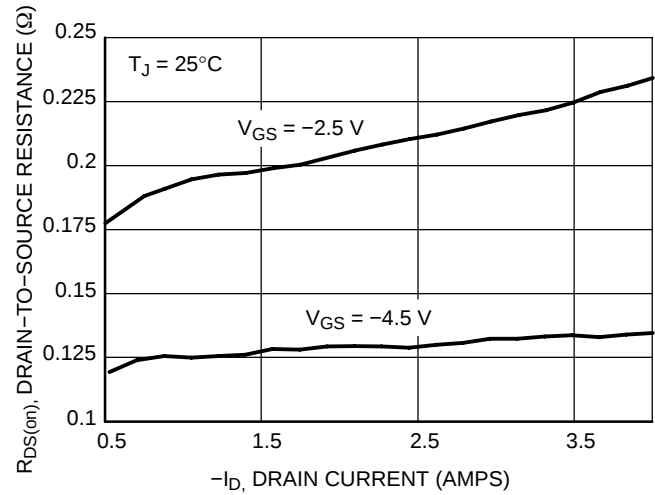


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

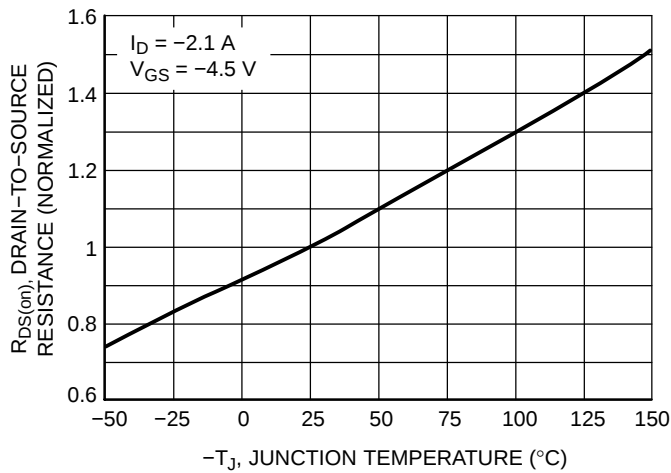


Figure 5. On-Resistance Variation with Temperature

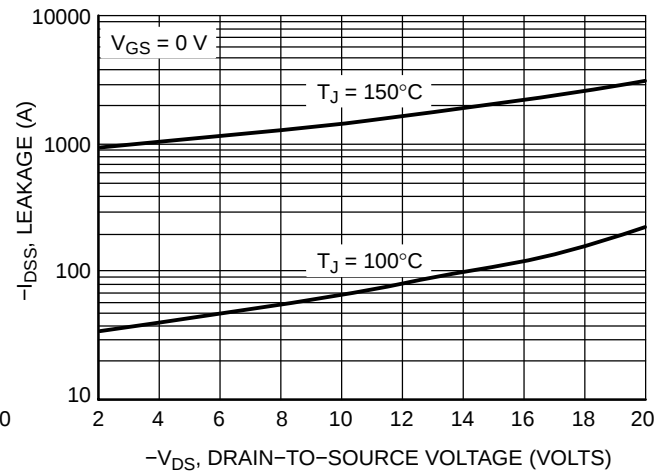


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL MOSFET PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

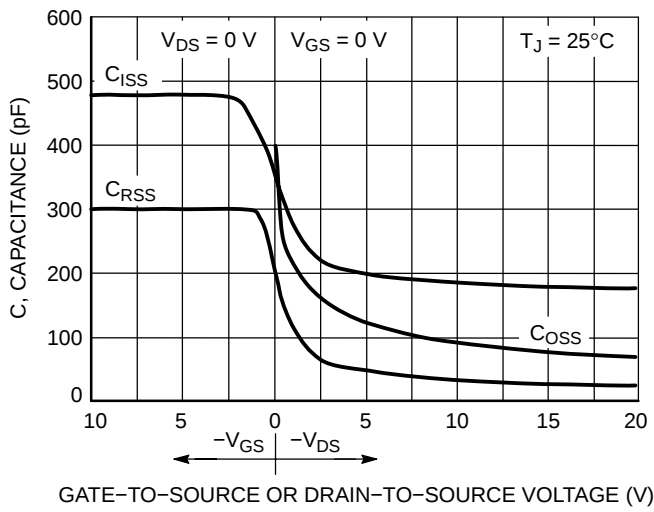


Figure 7. Capacitance Variation

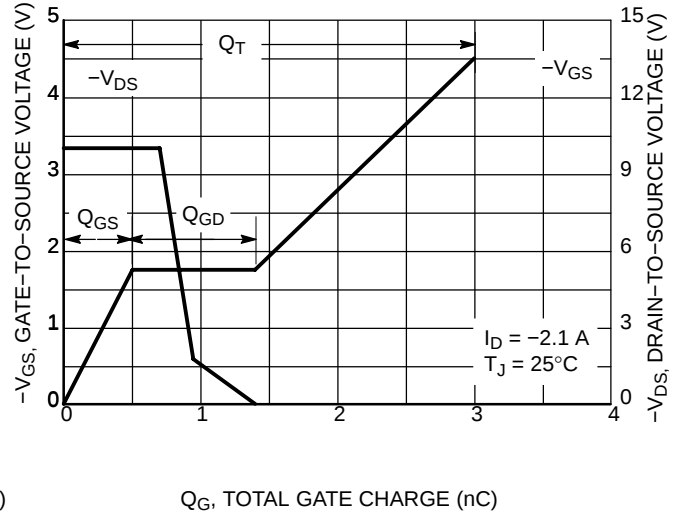


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

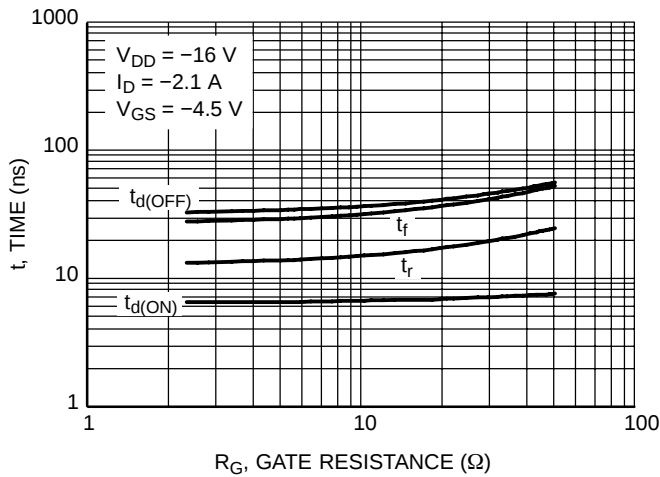


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

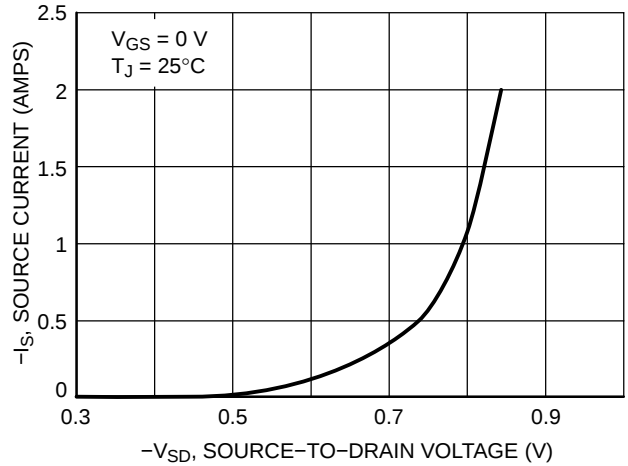


Figure 10. Diode Forward Voltage vs. Current

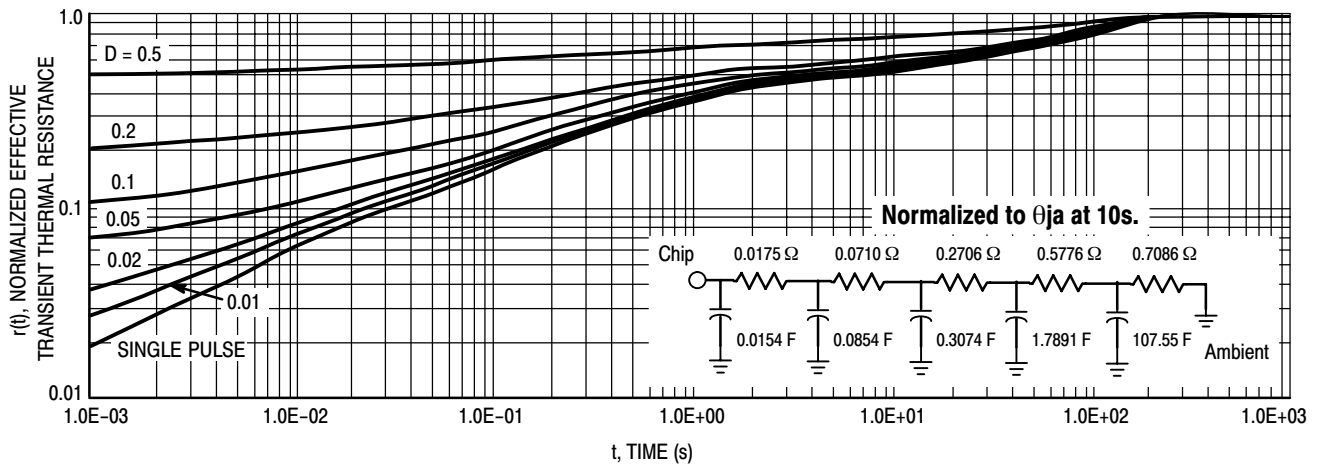


Figure 11. Thermal Response

TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

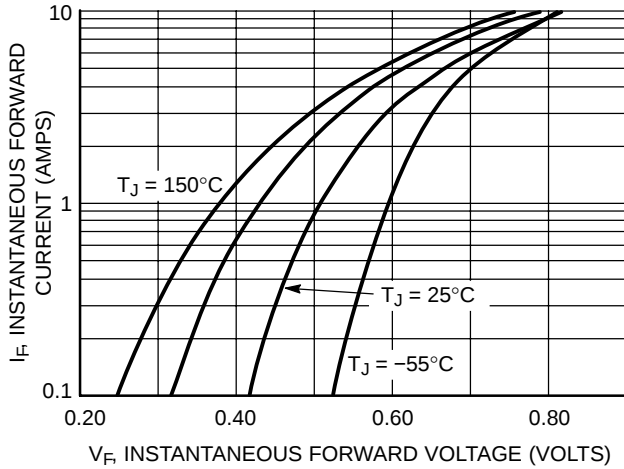


Figure 12. Typical Forward Voltage

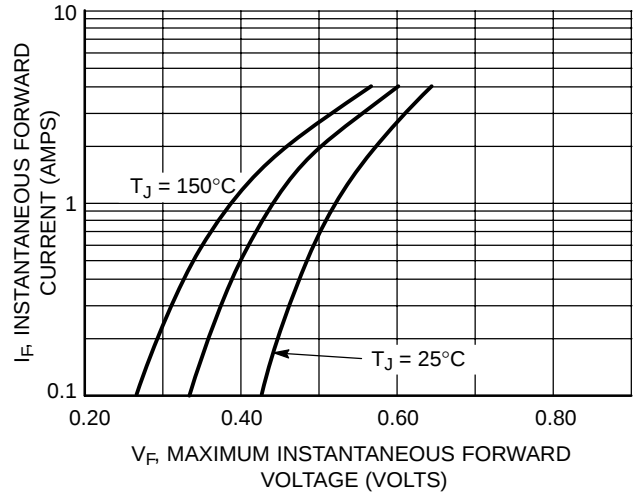


Figure 13. Maximum Forward Voltage

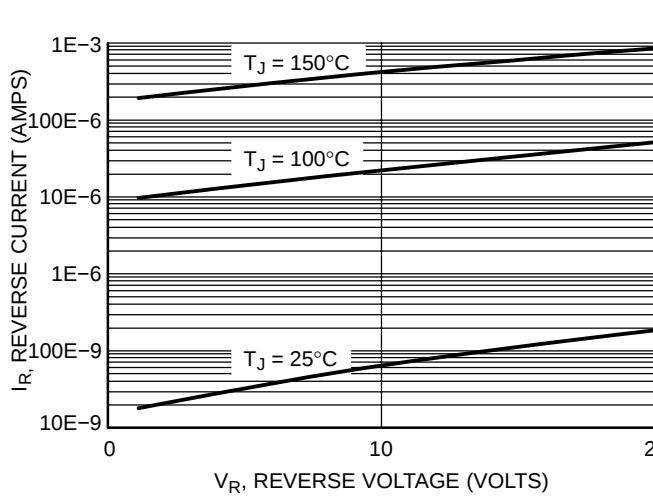


Figure 14. Typical Reverse Current

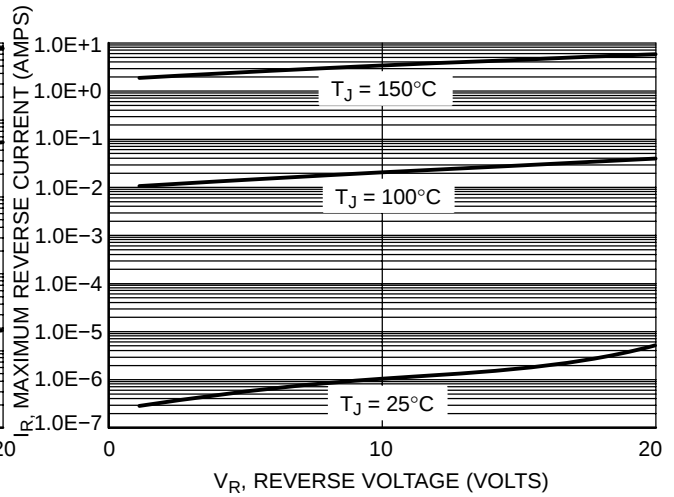


Figure 15. Maximum Reverse Current

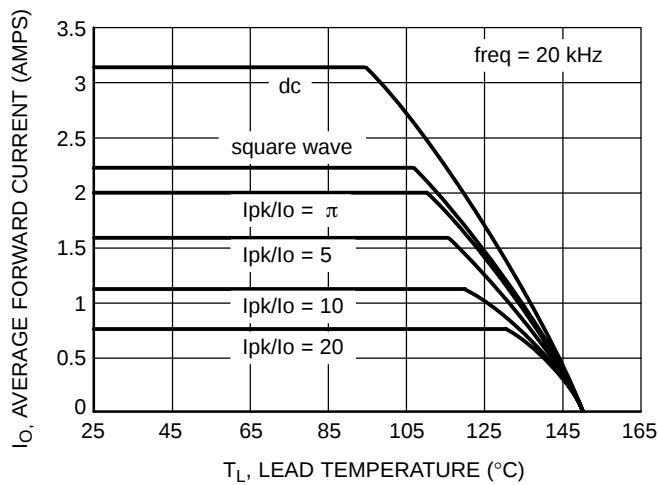


Figure 16. Current Derating

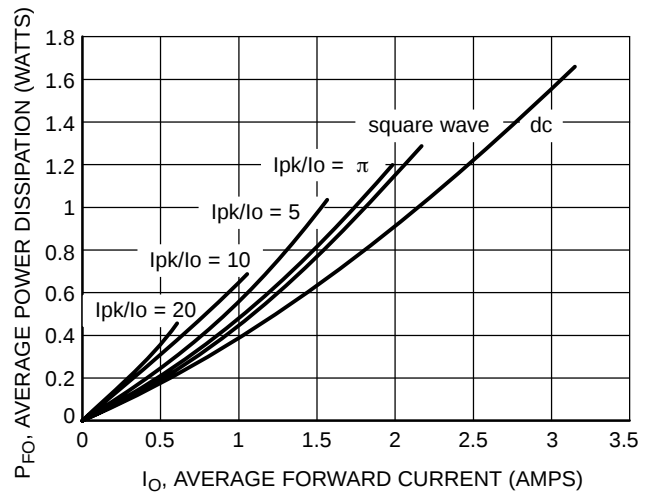


Figure 17. Forward Power Dissipation

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SOLDERING FOOTPRINT*

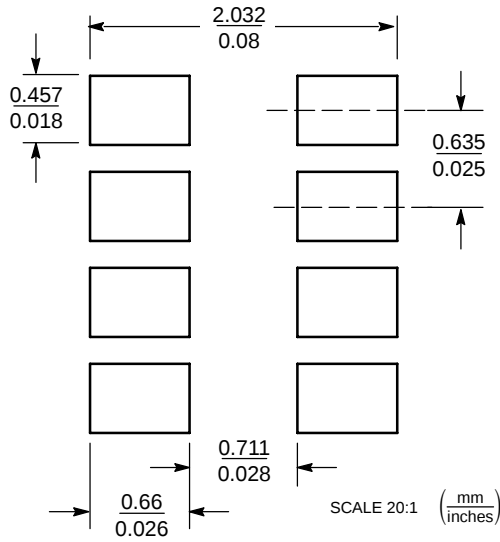


Figure 18. Basic

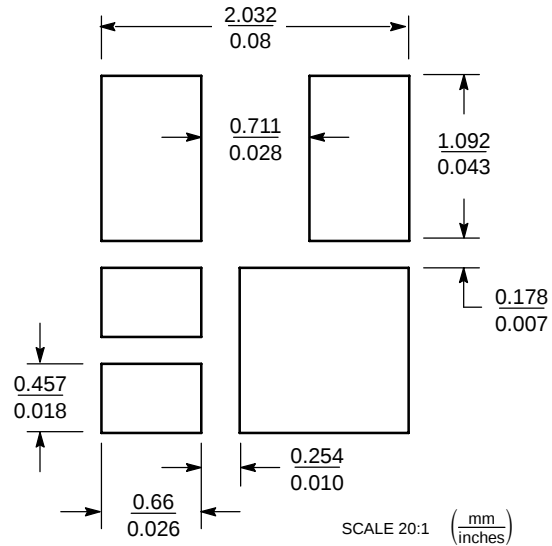


Figure 19. Style 3

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BASIC PAD PATTERNS

The basic pad layout with dimensions is shown in Figure 18. This is sufficient for low power dissipation MOSFET applications, but power semiconductor performance requires a greater copper pad area, particularly for the drain leads.

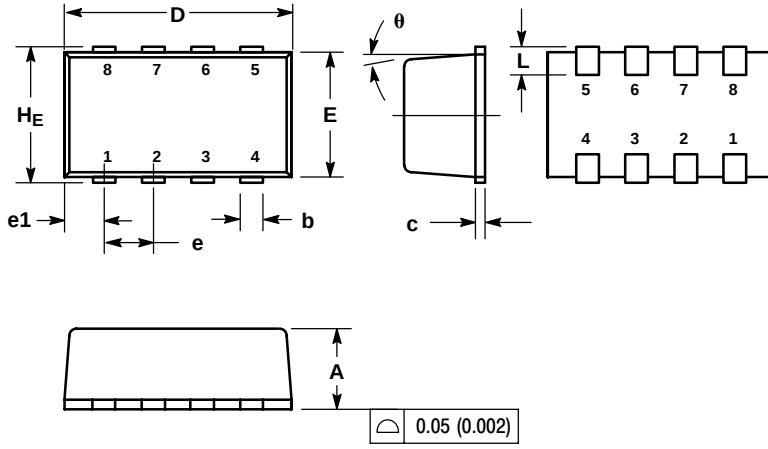
The minimum recommended pad pattern shown in Figure 19 improves the thermal area of the drain connections (pins 5, 6) while remaining within the confines

of the basic footprint. The drain copper area is 0.0019 sq. in. (or 1.22 sq. mm). This will assist the power dissipation path away from the device (through the copper lead-frame) and into the board and exterior chassis (if applicable) for the single device. The addition of a further copper area and/or the addition of vias to other board layers will enhance the performance still further.

NTHD4P02F

PACKAGE DIMENSIONS

ChipFET™
CASE 1206A-03
ISSUE G



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
H _E	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

STYLE 3:

- PIN 1. A
2. A
3. S
4. G
5. D
6. D
7. C
8. C

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